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1N4444 General Purpose Silicon Rectifier DO-35 Type Package

Absolute Maximum Ratings:

Continuous Reverse Voltage, V_R	50V
Average Forward Current, $I_{F(AV)}$	200mA
Repetitive Peak Forward Current, I_{FRM}	600mA
Forward DC Current, I_F	250mA
Non-Repetitive Peak Forward Current ($t = 1\mu s$), I_{FSM}	4A
Total Power Dissipation, P_{tot}	500mW
Operating Junction Temperature Range, T_J	-65° to +200°C
Storage Temperature Range, T_{stg}	-65° to +200°C
Lead temperature (During Soldering, 1/16" from case, 10sec)	+300°C

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 0.1mA$	440	-	550	mV
		$I_F = 1mA$	560	-	680	mV
		$I_F = 10mA$	690	-	820	mV
		$I_F = 100mA$	850	-	1000	mV
Breakdown Voltage	$V_{(BR)R}$	$I_R = 5\mu A$	70	-	-	V
Reverse Current	I_R	$V_R = 50V$	-	-	50	nA
		$V_R = 50V, T_A = +150^\circ C$	-	-	50	μA
Diode Capacitance	C_o	$V_R = 0, \text{Note 1}$	-	-	2	pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 10mA, \text{Recover to } 1mA$	-	-	7	ns

